This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

**IRHNJ597230 (2N7546U3)**

-200V, P-Channel, TID Hardened MOSFET in a SMD-0.5 package

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

\[ V_{SD} \text{[Diode Forward Voltage]}, \text{change maximum limit from } -5.5\text{V to } -5.0\text{V} \]

**RADIATION CHARACTERISTICS CHANGE:**

Table 1 Electrical Characteristics @ \( T_j = 25^\circ \text{C}, \text{Post Total Dose Irradiation} \)

\[ V_{SD} \text{[Diode Forward Voltage]}, \text{change maximum limit for } 100k\text{Rads(Si)} \text{ and } 300k\text{Rads(Si)} \text{ from } -5.5\text{V to } -5.0\text{V} \]

Reference Datasheet PD-94046

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**Reference**

GIDEP Form 97-5